

# 2SA1095

SILICON PNP EPITAXIAL TYPE (PCT PROCESS)

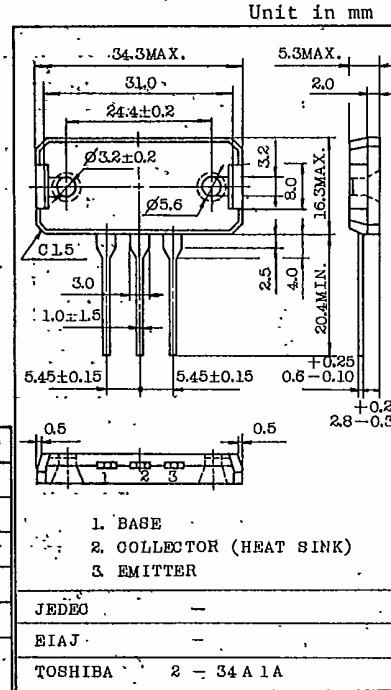
POWER AMPLIFIER APPLICATIONS.

FEATURES:

- High Breakdown Voltage :  $V_{CE0} = -160V$
- High Transition Frequency :  $f_T = 60MHz$  (Typ.)
- Complementary to 2SC2565.
- Recommended for 100W High-Fidelity Audio Frequency Amplifier Output Stage.

MAXIMUM RATINGS (Ta=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	$V_{CBO}$	-160	V
Collector-Emitter Voltage	$V_{CEO}$	-160	V
Emitter-Base Voltage	$V_{EBO}$	-5	V
Collector Current	$I_C$	-15	A
Emitter Current	$I_E$	15	A
Collector Power Dissipation (Tc=25°C)	$P_C$	150	W
Junction Temperature	$T_j$	150	°C
Storage Temperature Range	$T_{stg}$	-55~150	°C



Weight : 10.8g

ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	$I_{CBO}$	$V_{CB} = -160V, I_E = 0$	-	-	-50	$\mu A$
Emitter Cut-off Current	$I_{EBO}$	$V_{EB} = -5V, I_C = 0$	-	-	-50	$\mu A$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = -0.1A, I_B = 0$	-160	-	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = -0.01A, I_C = 0$	-5	-	-	V
DC Current Gain	$h_{FE(1)}$	$V_{CE} = -5V, I_C = -1A$	55	-	240	
	$h_{FE(2)}$	$V_{CE} = -5V, I_C = -5A$	40	-	-	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = -5A, I_B = -0.5A$	-	-	-2.0	V
Base-Emitter Voltage	$V_{BE}$	$V_{CE} = -5V, I_C = -5A$	-	-	-2.0	V
Transition Frequency	$f_T$	$V_{CE} = -10V, I_C = -1A$	-	60	-	MHz
Collector Output Capacitance	$C_{ob}$	$V_{CB} = -10V, I_E = 0, f = 1MHz$	-	350	-	pF

Note :  $h_{FE(1)}$  Classification R : 55~110, 0 : 80~160, Y : 120~240

TOSHIBA CORPORATION

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